

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-10. (Canceled)

11. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a redistribution layer over a semiconductor wafer which includes an integrated circuit and an interconnect electrically connected with the integrated circuit, the redistribution layer electrically connecting with a pad which is a part of the interconnect and including a first portion located over the pad and a second section other than the first portion;

forming an external terminal on the second section of the redistribution layer;

forming a first resin layer having a side surface so that at least a part of the first resin layer is placed on the redistribution layer;

forming a second resin layer over the first resin layer and in direct contact with the semiconductor wafer so as to cover the side surface of the first resin layer, the first and second resin layers having no wiring therebetween; and

cutting the semiconductor wafer.

12. (Original) The method of manufacturing a semiconductor device as defined in claim 11, comprising:

forming the first resin layer to cover the redistribution layer excluding a region in which the external terminal is formed, and

forming the second resin layer to cover at least a lower part of the external terminal.

13. (Original) The method of manufacturing a semiconductor device as defined in claim 11, further comprising:

forming an insulating layer before forming the redistribution layer,

wherein the redistribution layer is formed on the insulating layer.

14. (Original) The method of manufacturing a semiconductor device as defined in claim 11,

wherein the semiconductor wafer includes a first region and a plurality of second regions, each of the second regions being surrounded by the first region,

wherein the first resin layer and the second resin layer are formed only in the second region, and

wherein the semiconductor wafer is cut along the first region.

15. (Original) The method of manufacturing a semiconductor device as defined in claim 12,

wherein the semiconductor wafer includes a first region and a plurality of second regions, each of the second regions being surrounded by the first region,

wherein the first resin layer and the second resin layer are formed only in the second region, and

wherein the semiconductor wafer is cut along the first region.

16. (Original) The method of manufacturing a semiconductor device as defined in claim 13,

wherein the semiconductor wafer includes a first region and a plurality of second regions, each of the second regions being surrounded by the first region,

wherein the first resin layer and the second resin layer are formed only in the second region, and

wherein the semiconductor wafer is cut along the first region.

17. (Original) The method of manufacturing a semiconductor device as defined in claim 11, comprising:

forming a part of the second resin layer which covers the side surface of the first resin layer, in a upper part and along an edge portion of the second region.

18. (Original) The method of manufacturing a semiconductor device as defined in claim 11,

wherein the second resin layer is formed by using a resin that is sensitive to radiation and by applying lithographic technology.

19. (Withdrawn) The method of manufacturing a semiconductor device as defined in claim 11,

wherein the second resin layer is formed by ejecting a resin by using an ink-jet method.

20. (Withdrawn) The method of manufacturing a semiconductor device as defined in claim 11,

wherein the second resin layer is formed by applying a resin by using a printing method.

21-22. (Canceled)

23. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a wiring pattern over a semiconductor wafer which includes an integrated circuit and an interconnect electrically connected with the integrated circuit, the wiring pattern electrically connecting with a pad which is a part of the interconnect and including a first portion located over the pad and a second section other than the first portion;

forming an external terminal on the second section of the wiring pattern;

forming a first resin layer having a side surface so that at least a part of the first resin layer is placed on the wiring pattern;

forming a second resin layer over the first resin layer and in direct contact with the semiconductor wafer so as to cover the side surface of the first resin layer, the first and second resin layers having no wiring therebetween; and

cutting the semiconductor wafer.

24. (Previously Presented) The method of manufacturing a semiconductor device as defined in claim 23, the second resin layer extending further along a surface of the semiconductor wafer than the first resin layer so as to cover a surface area of the semiconductor wafer that is not covered by the first resin layer.

25. (Previously Presented) The method of manufacturing a semiconductor device as defined in claim 11, the second resin layer extending further along a surface of the semiconductor wafer than the first resin layer so as to cover a surface area of the semiconductor wafer that is not covered by the first resin layer.

26. (New) A method of manufacturing a semiconductor device comprising:
forming a redistribution layer over a semiconductor wafer with a passivation film formed thereon, the semiconductor wafer including an integrated circuit and an interconnect electrically connected with the integrated circuit, the redistribution layer electrically connecting with a pad which is a part of the interconnect and including a first portion located over the pad and a second section other than the first portion;

forming an external terminal on the second section of the redistribution layer;

forming a first resin layer on the passivation film, the first resin layer having a side surface so that at least a part of the first resin layer is placed on the redistribution layer;

forming a second resin layer over the first resin layer and in direct contact with the passivation film so as to cover the side surface of the first resin layer, the first and second resin layers having no wiring therebetween; and

cutting the semiconductor wafer.

27. (New) A method of manufacturing a semiconductor device comprising:

forming a wiring pattern over a semiconductor wafer with a passivation film formed thereon, the semiconductor wafer including an integrated circuit and an interconnect electrically connected with the integrated circuit, the wiring pattern electrically connecting with a pad which is a part of the interconnect and including a first portion located over the pad and a second section other than the first portion;

forming an external terminal on the second section of the wiring pattern;

forming a first resin layer on the passivation film, the first resin layer having a side surface so that at least a part of the first resin layer is placed on the wiring pattern;

forming a second resin layer over the first resin layer and in direct contact with the passivation film so as to cover the side surface of the first resin layer, the first and second resin layers having no wiring therebetween; and

cutting the semiconductor wafer.